

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A CVD system provided with a plasma generator, comprised of a conductive upper and lower plates and a circumferential wall made of an insulator, having a plasma generation chamber separated from a film deposition chamber in which a substrate is arranged, wherein a material gas is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes of a said lower plate, and a thin film is deposited on the substrate, said CVD system further comprising:

a cleaning gas feeder provided to said plasma generator,

said lower plate is connected to ground, and

each of said introduction holes is designed to pass the radicals only to the film deposition chamber,

wherein a cleaning gas is introduced through said cleaning gas feeder to produce plasma in the plasma generator and generate radicals, and the radicals are introduced through said introduction holes to said film deposition chamber to strike the substrate and thereby clean the substrate and further the film is deposited on the substrate within the same chamber as the substrate is not moved.

2. (Original) A CVD system as set forth in claim 1, wherein said cleaning gas is a gas selected from O₂, H₂, F₂, N₂, dilute gas, and halide gas or a gas comprised of a suitable mixture of the plural gases.

3. (Withdrawn) A substrate cleaning method comprising:

depositing a silicon-based film on a substrate,

converting the silicon-based film to a crystalline silicon film by laser annealing,

depositing a gate insulating film on said crystalline film by a CVD system comprised of a separate film deposition chamber and plasma generation chamber using a lower plate with introduction holes, wherein said lower plate is connected to ground and each of the introduction holes is designed to pass radical only in plasma.

generating plasma by use of a cleaning gas in said CVD system at a stage before forming the gate insulating film and emitting only the radicals in the plasma through the introduction holes of the lower plate on the crystalline silicon film to clean its surface.

4. (Withdrawn) A substrate cleaning method as set forth in claim 3, wherein said cleaning gas is a gas selected from O₂, H₂, F₂, N₂, dilute gas, and halide gas or a gas comprised of a suitable mixture of the plural gases.

5. (Currently Amended) A CVD system provided with a plasma generator comprised of a conductive upper and lower plates and a circumferential wall made of an insulator, having a plasma generation chamber separated from a film deposition chamber in which a substrate is arranged, wherein a material gas is directly supplied into the film deposition chamber, radicals in the plasma are introduced into the film deposition chamber from the plasma generator through introduction holes, and a thin film is deposited on the substrate, said CVD system further comprising:

a cleaning gas feeder provided to said plasma generator, and

a diameter of each of said introduction holes is designed to pass the radicals only to the film deposition chamber,

wherein a cleaning gas is introduced through said cleaning gas feeder to produce plasma in the plasma generator and generate radicals, and the radicals are introduced through said introduction holes to said film deposition chamber to strike the substrate and

thereby clean the substrate and further the film is deposited on the substrate within the same chamber as the substrate is not moved.

6. (Previously Presented) A CVD system as set forth in claim 1, wherein said cleaning gas is a gas selected from the group consisting of O₂, H₂, F₂, N₂, dilute gas, halide gas, and mixtures thereof.